

Features

- Low On-Resistance: RDS(ON)
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected up to 2KV
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

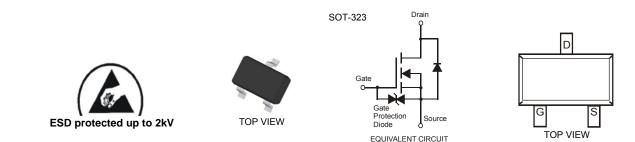


DMN2004WK

N-CHANNEL ENHANCEMENT MODE MOSFET

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)



Ordering Information (Note 4)

Part Number		Case	Packaging				
	DMN2004WK-7	SOT-323	3000/Tape & Reel				
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.							

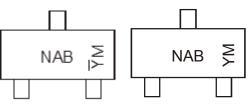
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



Chengdu A/T Site

Shanghai A/T Site

NAB = Product Type Marking Code $\gamma M = Date Code Marking for SAT (Shanghai Assembly/ Test site)$ $\gamma M = Date Code Marking for CAT (Chengdu Assembly/ Test site)$ Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Year	2009		2010 2011		2012		2013		2014	2	2015		
Code	W		Х		Y		Z			В		С	
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec	
Code	1	2	3	4	5	6	7	8	9	0	N	D	



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Char	acteristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +85°C	۱ _D	540 390	mA
Pulsed Drain Current (Note 6)			I _{DM}	1.5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	200	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	C°

Notes: 5. Device mounted on FR-4 PCB.

6. Pulse width $\leq 10\mu S$, Duty Cycle $\leq 1\%$.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

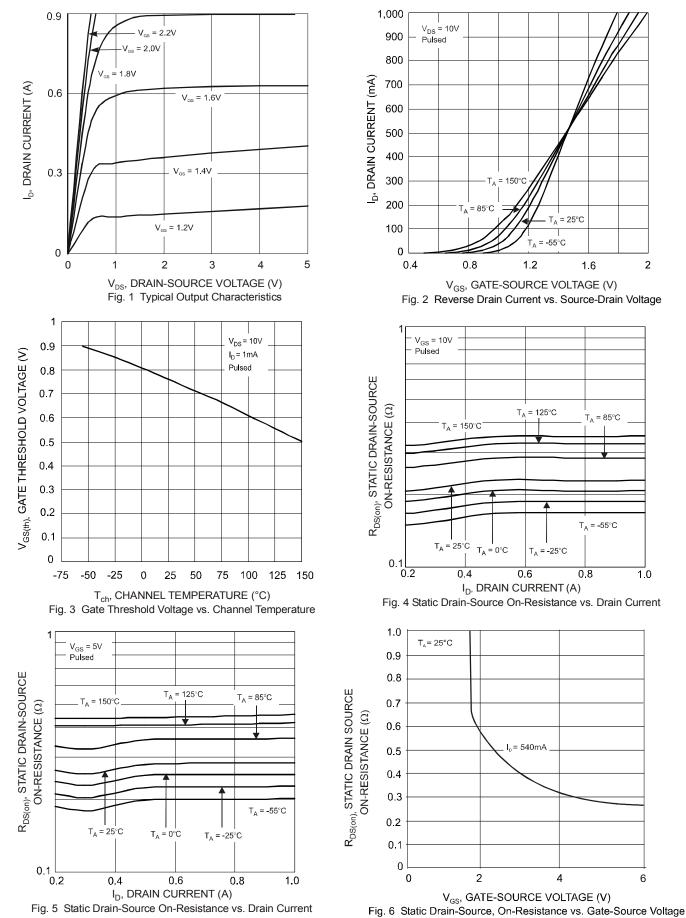
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)						-	
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	IDSS		_	1	μA	V _{DS} = 16V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	—	±1	μA	V_{GS} = ±4.5V, V_{DS} = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.5	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		_	0.4	0.55 0.70 0.9	Ω	V_{GS} = 4.5V, I_{D} = 540mA	
Static Drain-Source On-Resistance	R _{DS (ON)}		0.5 0.7			V _{GS} = 2.5V, I _D = 500mA	
	. ,					V _{GS} = 1.8V, I _D = 350mA	
Forward Transfer Admittance	Y _{fs}	200	—	_	ms	V _{DS} =10V, I _D = 0.2A	
Diode Forward Voltage (Note 7)	V _{SD}	0.5		1.4	V	V _{GS} = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS(Note 8)							
Input Capacitance	Ciss	_	_	150	pF		
Output Capacitance	C _{oss}	_		25	pF	$V_{DS} = 16V, V_{GS} = 0V$ = f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	_	20	pF		

Notes: 7. Short duration pulse test used to minimize self-heating effect.

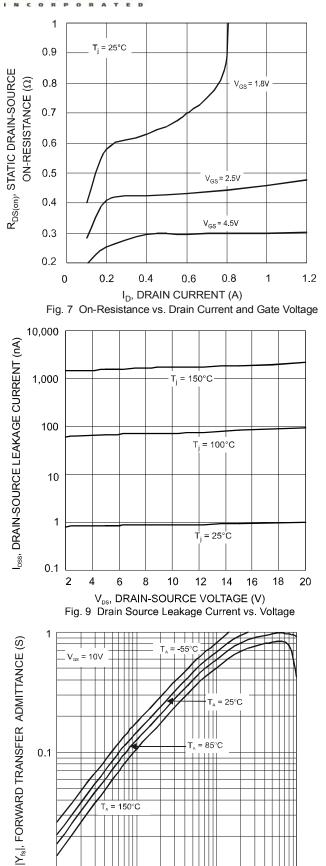
8. Guaranteed by design. Not subject to production testing.

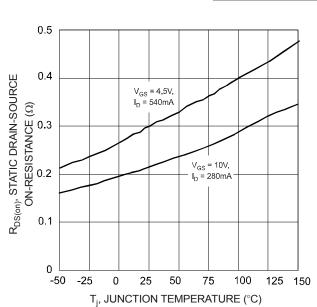


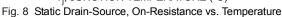


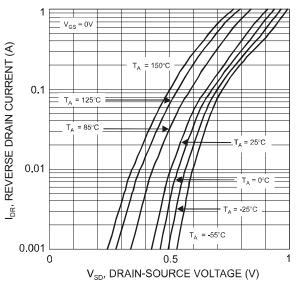




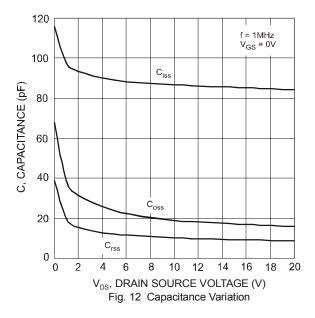












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I_D, DRAIN CURRENT (mA)

Fig. 11 Forward Transfer Admittance vs. Drain Current

0.01

1

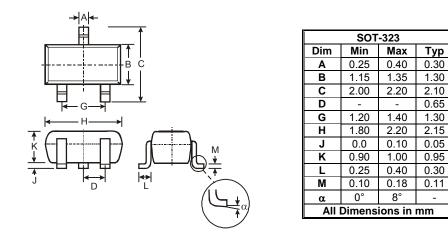
1000

100



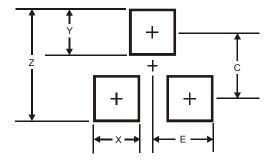
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
E	1.0



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